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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										備考	
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μS)	f _{αb} f _r * (Mc)		C _{ob} (pF)
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
- 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)										外形	備考							
				V _{CEO} (V)	V _{EMO} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CMO} 最大値		直流又はパルス hFE		バイアス		h _{FE} *	h _{FE} *	h _{FE} *	h _{FE} *			f _β f _T *	C _{ob} (pF)	r _{bb} h _{ibreal} *				
									μA	V _{CE} (V)	V _{CE} (V)	I _C (mA)	V _{CE} (V)	I _E (mA)													
2SA773	ソニー	RF. PA	Si. EP	-60	-6	-1A	750	120	-0.2	-25	250	-2	-100	-2	10					65*	25	259	2SC1475 とコンブリ				
* 774	松下	RF. LN	Si. EP	-35	-5	-50	150	175	-0.1	-10	540	-5	-2	-5	2					3500	3	60	120*	5	100	243	
* 775	日立	PA	Si. T	-100	-4	-700	12.5W (T _c =25°C)	150	-10		90	-4	-50	-4	30								30*	35	25	268	
* 776	東芝	RF. LN	Si. EP	-55	-5	-50	200	150	-0.1	-30	300	-6	-2	-6	1	285	7300	1	21			180*	3	35	195		
* 777	松下	PA	"	-80	-5	-500	750	135	-0.1	-20	160	-10	150	-10	50							120*	20	2k*	165	2SC1509 とコンブリ	
* 778	日立	SW	Si. T	-150	-5	-50	200	125	-1	-100	100	-3	-15	-3	15							50*	<4		138		
* 779	"	RF. PA. SW	Si. E	-35	-5	-1.5A	10W (T _c =25°C)	150	-20	-30	60-200	-2	-500	-2	200	t _{on} =130nS, t _{off} =550nS						110*	50		234		
* 780	"	PA. SW	"	-50	-4	-1A	10W (T _c =25°C)	150	-1	-30	120	-4	-50	-4	50							120*	8		234	2SC1517 とコンブリ	
* 781	"	SW. RF	"	-20	-4	-200	200	125	-0.2	-16	20-200	-0.5	-30	-1	30	t _{on} <70nS, t _{off} <120nS						550*	25		138		
* 782	東洋電具	RF. Conv. Mix Osc. PA. AF	"	-80	-5	-30	150	125	-1	-50	150	-6	-1	-6	1					7.1k	0.4	6.7	200*	3	C _e r _{bb} 160pS	235	
* 783	"	"	"	-50	-5	-30	150	125	-1	-30	150	-6	-1	-6	1					7.1k	0.4	6.7	200*	3	C _e r _{bb} 160pS	235	
* 784	"	"	"	-25	-5	-30	150	125	-1	-15	130	-6	-1	-6	1					7.1k	0.4	6.7	200*	3	C _e r _{bb} 160pS	235	
* 785	"	"	"	-80	-5	-50	150	125	-1	-50	150	-3	-10	-5	1					6.7k	0.8	10	180*	6.5	C _e r _{bb} 150pS	235	
* 786	"	"	"	-50	-5	-50	150	125	-1	-30	150	-3	-10	-5	1					6.7k	0.8	10	180*	6.5	C _e r _{bb} 150pS	235	
* 787	"	"	"	-20	-5	-50	150	125	-1	-15	150	-3	-10	-6	1					6.7k	0.8	10	180*	6.5	C _e r _{bb} 150pS	235	
* 788	"	RF. Conv. Mix Osc. PA. AF. LN	"	-50	-5	-30	150	125	-1	-30	150	-3	-10	-6	1	NF=2dB (f=1kHz) 7.1k						200*	3	C _e r _{bb} 160pS	235		
* 789	"	"	"	-25	-5	-30	150	125	-1	-15	150	-3	-10	-6	1	NF=2dB (f=1kHz) 7.1k						200*	3	C _e r _{bb} 160pS	235		
* 790	"	RF. Conv. Mix Osc. PA	"	-40	-6	-300	300	125	-1	-24	10,000	-5	-100	-5	10							200*	3	C _e r _{bb} 100pS	235		
* 791	"	"	"	-25	-6	-300	300	125	-1	-15	10,000	-5	-100	-5	10							200*	3	C _e r _{bb} 100pS	235		
* 792																											
* 793																											
* 794	松下	PA	Si. EP	-100	-5	-500	1.2W	150	-1	-100	160	-10	-150	-10	50							120*	20	3.5k*	222	2SC1567 とコンブリ	
* 795	"	"	"	-150	-5	-250	10W (T _c =30°C)	150	-30	-60	120	-10	-100	-10	50							120*	15	15	236	2SC1565 とコンブリ	
* 796	新日無	SW	"	-30	-10	-300	300	125	-1	-20	40,000	-6	-100			t _{on} <600nS, t _{off} <1.2μS									138	2SC1432 とコンブリ	
* 797																											
* 798	三菱	Diff. LN	Si. EP	-50	-5	-100	200 unit	125	-0.1	-35	250- 1200	-6	1	-6	1	ΔV _{BE} <10mV hFE _小 /hFE _大 =0.8-1.0						100*	3.0		274A	2素子複合	
* 799	富士通	SW	"	-60	-5	-1.5A	1W	200	-0.5	-50	54	-1	-500			t _{on} <45nS, t _{off} <110nS t _{arr} <80nS									84C		
* 800	日電	RF	Si. E	-20	-3	-30	250	200	-0.1	-15	60	-10	-10	-10	10	S ₂₁ ² >5dB (10V, 10mA, 1GHz)						2500*	0.9		50C		
* 801	"	"	"	-20	-3	-50	300	200	-0.1	-10	90	-10	-15	-5	15	S ₂₁ ² =10dB (10V, 20mA, 1GHz)						4000*	1.2		130		
* 802	東洋電具	SW	Si. TP	-130	-5	-30	150	125	-1	-80	56-270	-3	-5	-5	2							50*	8		235		